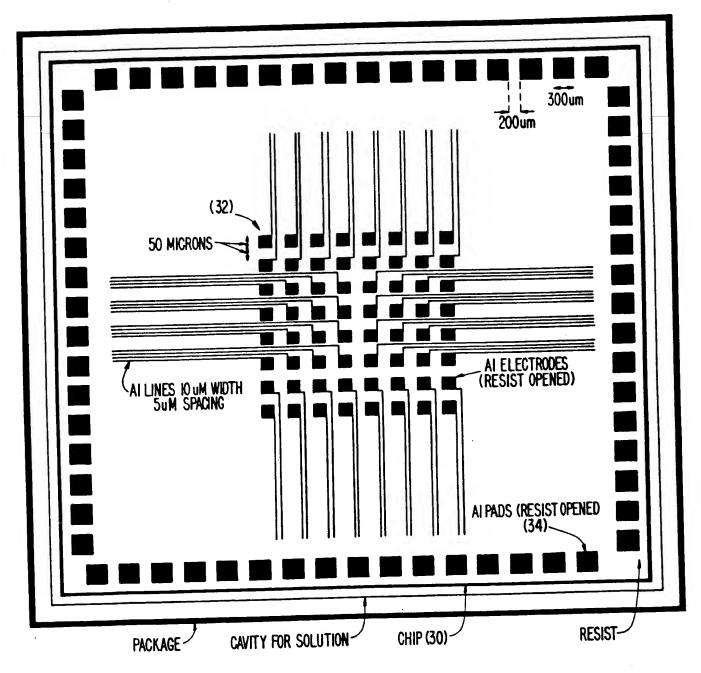
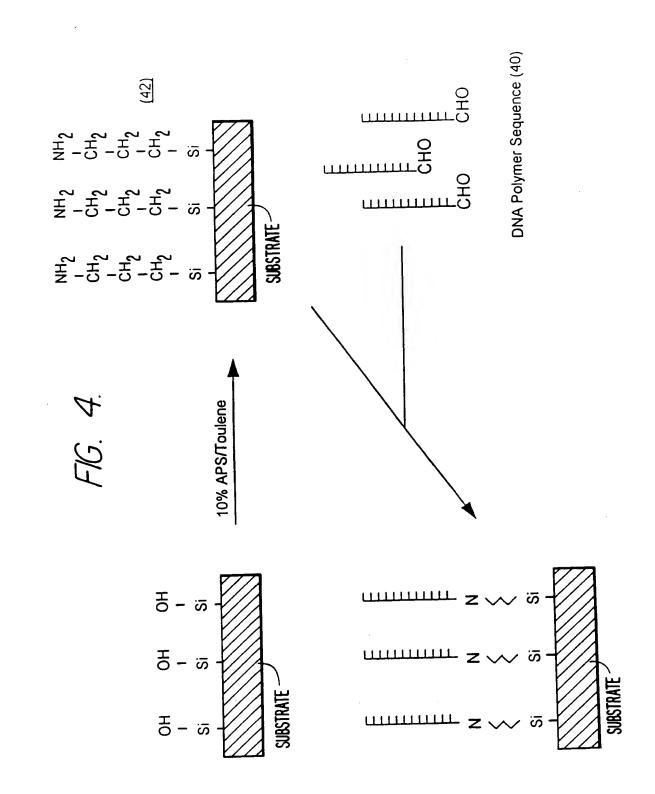
4 METAL (12) 严3 F16. 1 ML-2 METAL (12) MICROLOCATION I (ML-1) METAL (12) INSULATOR (5:02)-

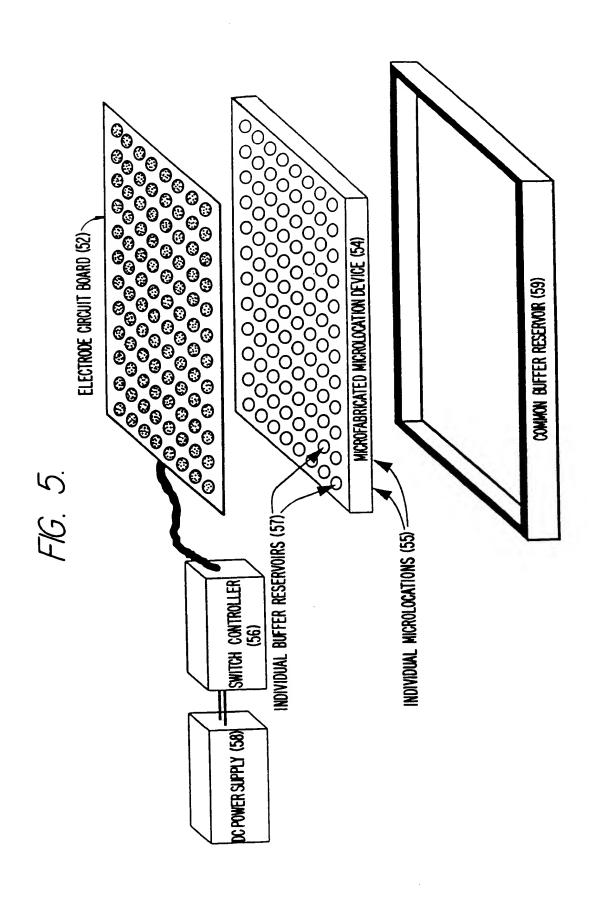
- INSULATOR (Si02) -NETAL OXIDE LAYER (20) BINDING ENTITY LAYER (26)~ ATTACHMENT LAYER (24) METAL (12) PERMEATION LAYER (22) Si3N4~

F16. 2.

FIG. 3.

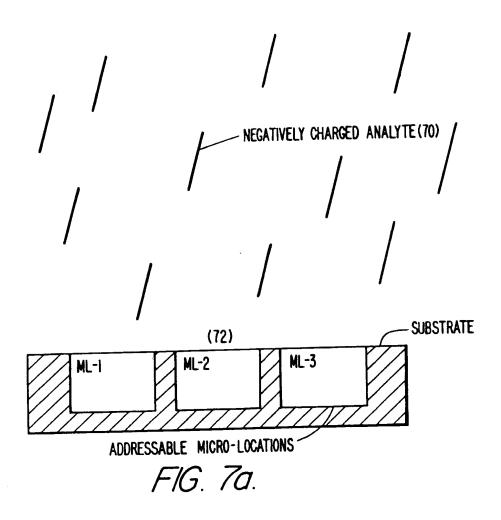


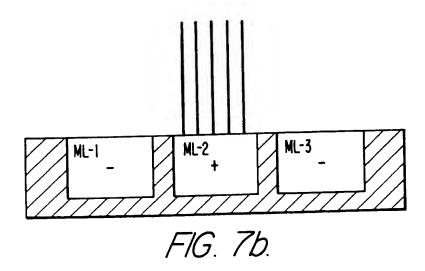




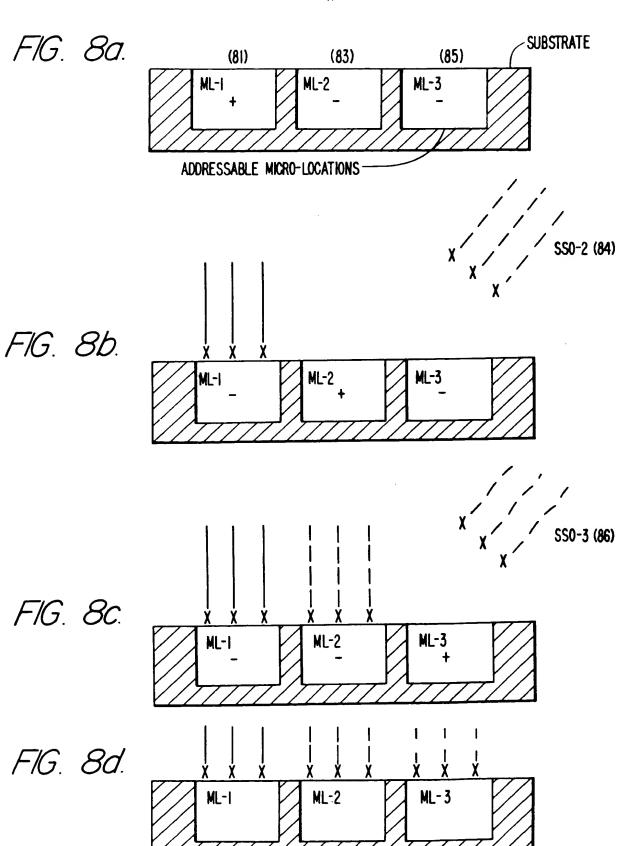
| BODY OF DEVICE | (54) ELECTRODE CIRCUIT BOARD (52) MICROLOCATION 2 (55)
(WITH BINDING ENTITY 2) N PERMEATION LAYER/SUPPORT ATTACHMENT LAYER BINDING ENTITY LAYER INDIVIDUAL BUFFER RESERVOIR 2 (57) F1G. 6. MICROLOCATION I (55) (WITH BINDING ENTITY I) ELECTRODE (62) INDIVIDUAL BUFFER RESERVOIR I (57),

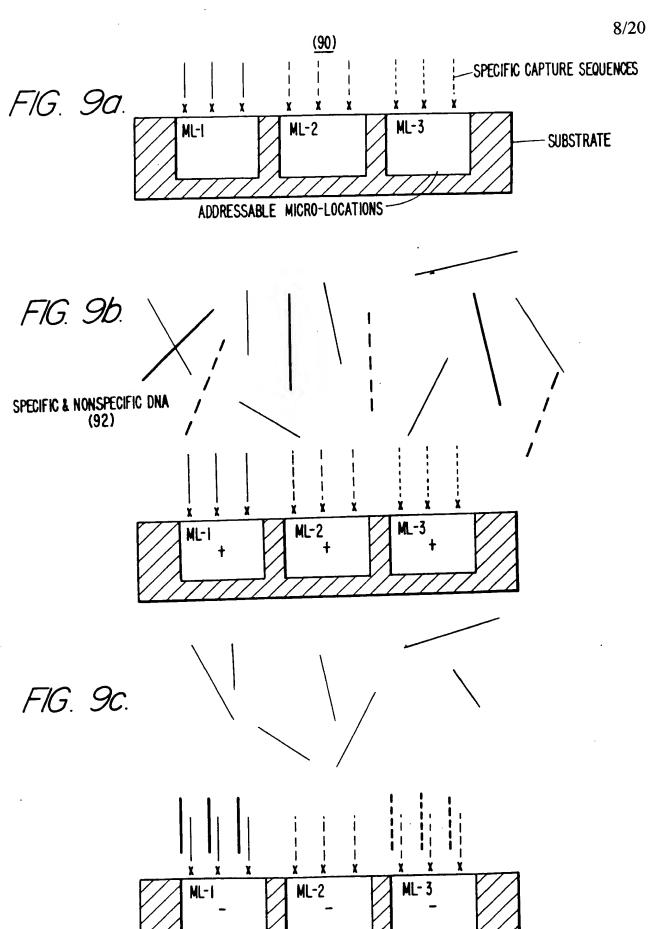
COMMON BUFFER RESERVOIR (59)

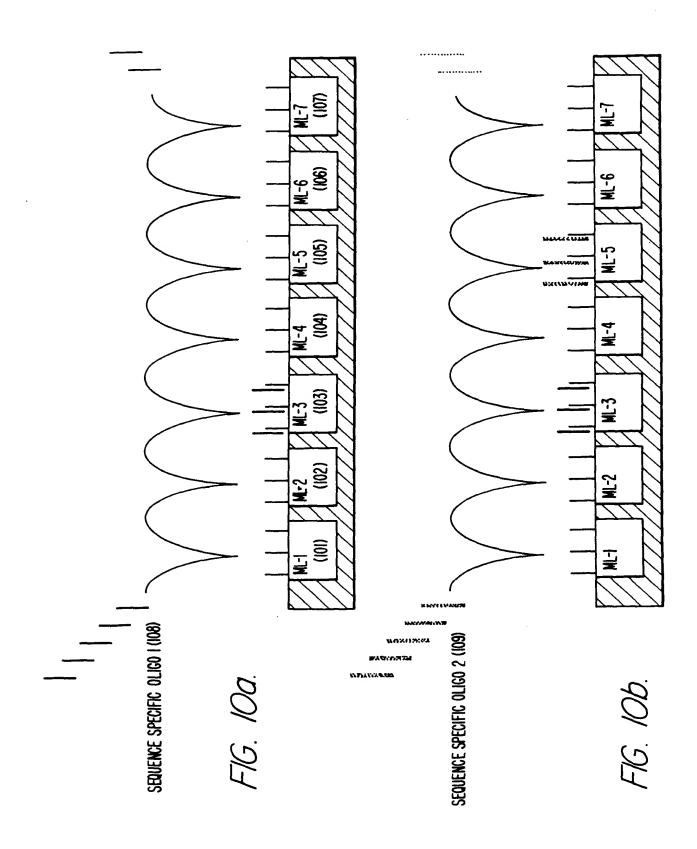


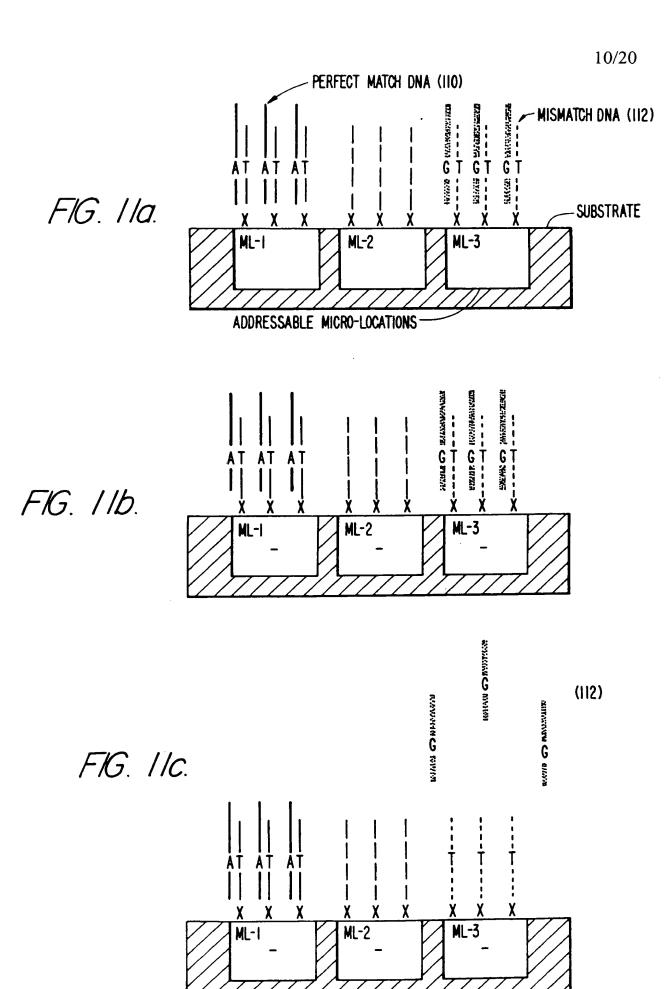












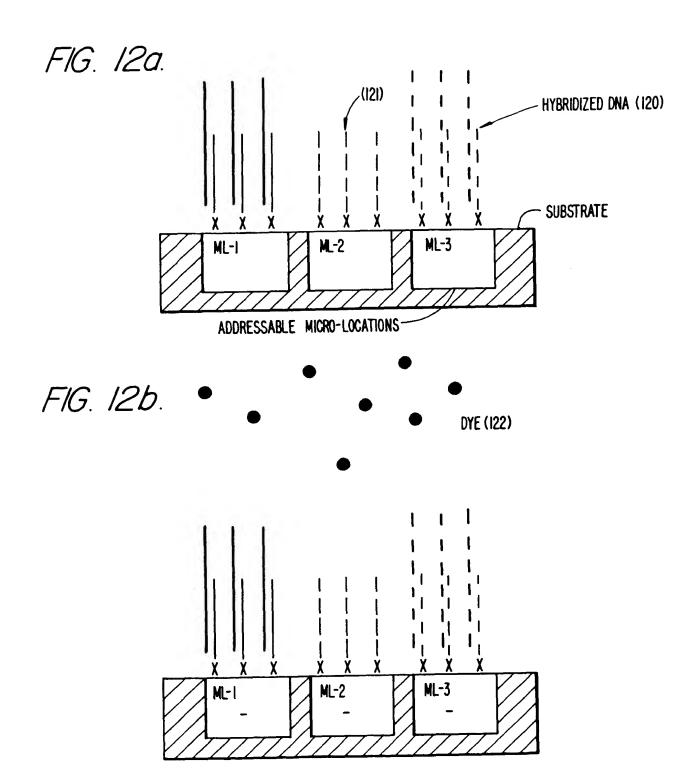
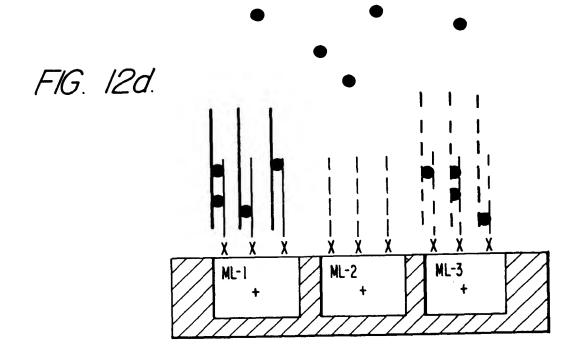
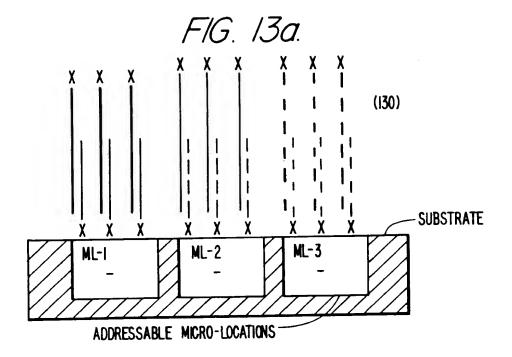


FIG. 12c. ML-2





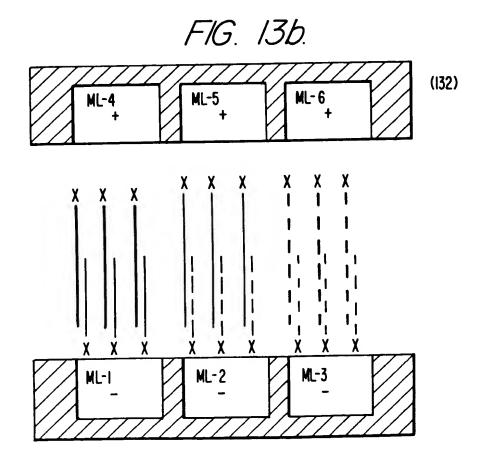
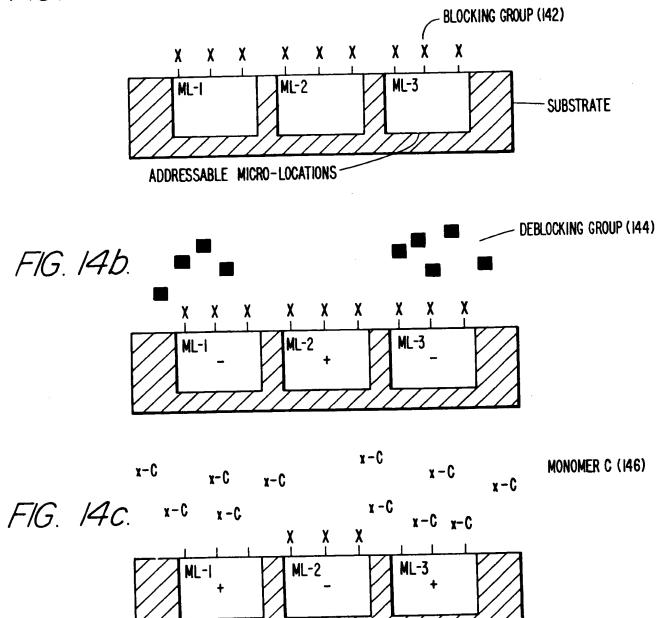
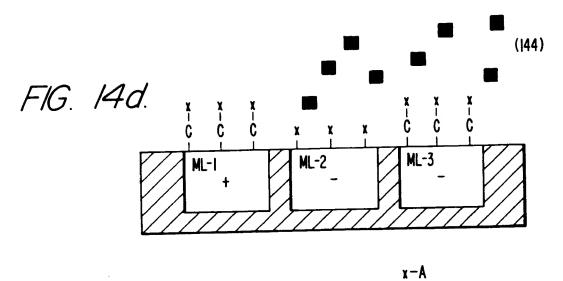
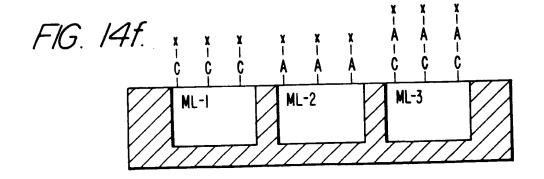
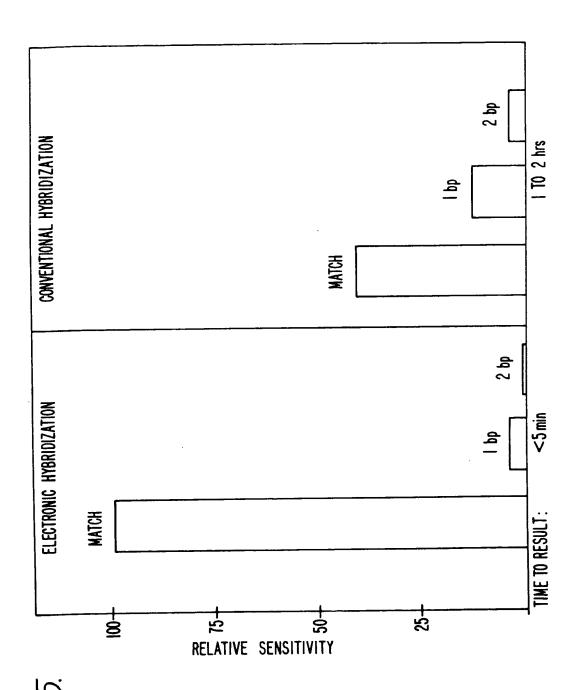


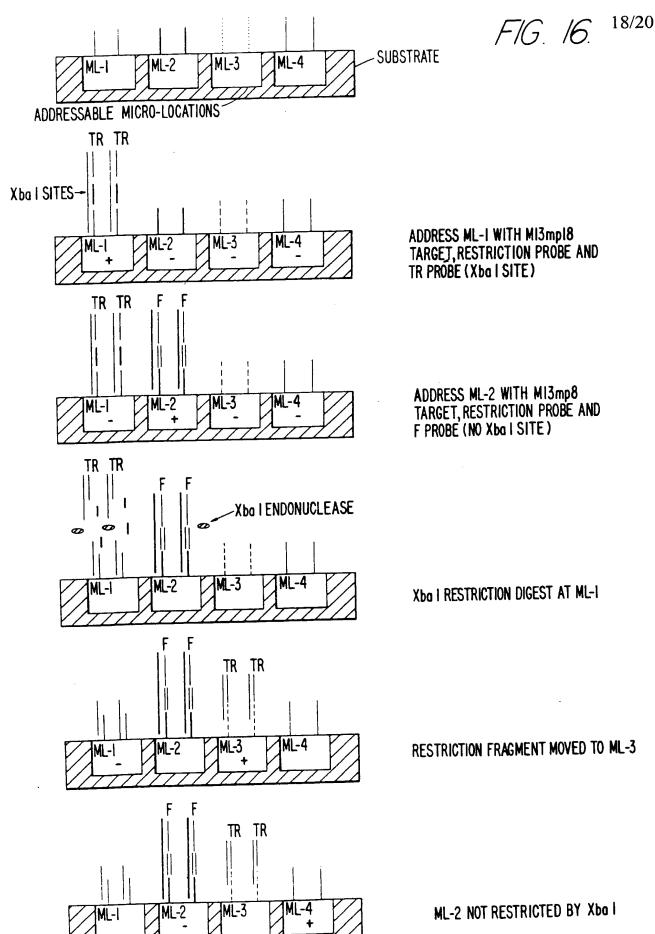
FIG. 14a.

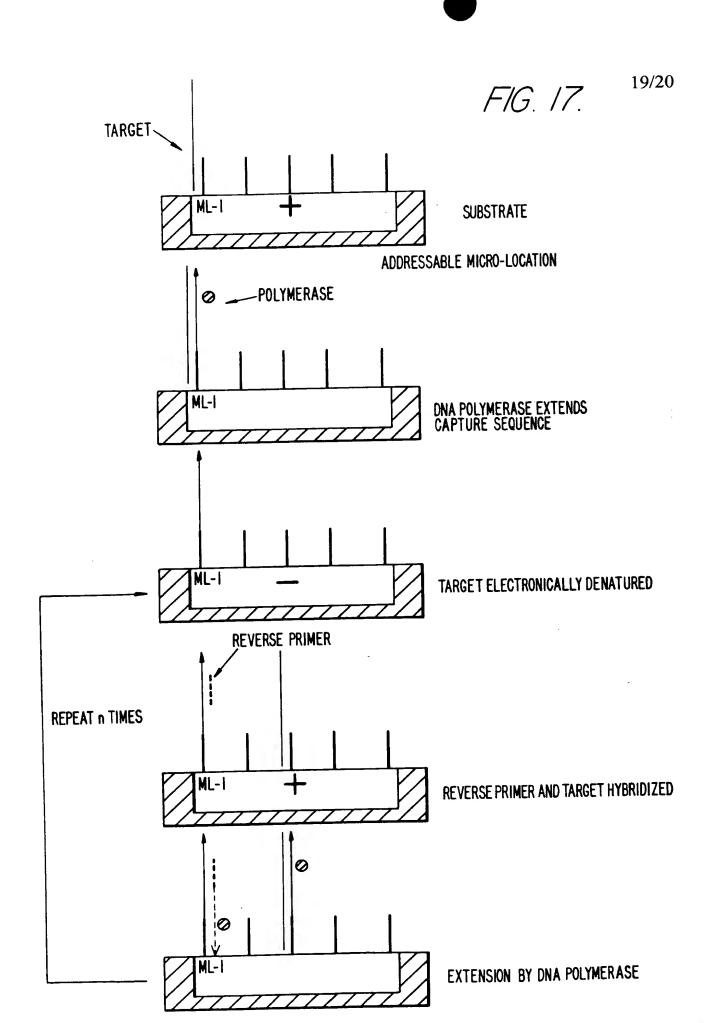












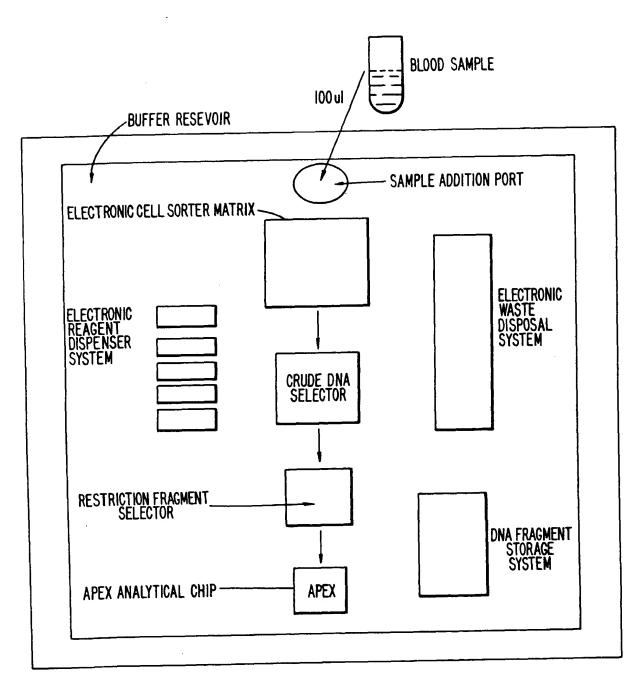


FIG. 18.